## Switching loss measurement for Wide-bandgap semiconductors

- In switching cell measurement (classic double pulse) for GaN and SiC
- Commutation loop current measurement
- Low additional inductance of 300 pH
- Bandwidth of 500 MHz
- High resolution control signal
- Up to 4 gate signals

- Configuration script
- Pulse and dead time resolution of 250 ps
- Coil for measurement purposes
- Calibrated up to 100 MHz
- Low stray field due to toroid shape
- Low HF losses due to litz wire
- Pulse resistant up to 150 A because no magnetic material is used
- Parameters of the measurement seen in the picture below
- U_DC $=600 \mathrm{~V}$
- I_L=20 A
- $L=7 u H$
- $\mathrm{dU} / \mathrm{dt}=70 \mathrm{~V} / \mathrm{ns}$--> 600 V in 8.5 ns !!!
- $\mathrm{dl} / \mathrm{dt}=18 \mathrm{~A} / \mathrm{ns}$


